

# MN74HC221/MN74HC221S

## Dual Monostable Multivibrators with Clear

### Outline

The MN74HC221/MN74HC221S is constituted by 2-circuit monostable multivibrators supported by the high speed silicon gate CMOS technique.

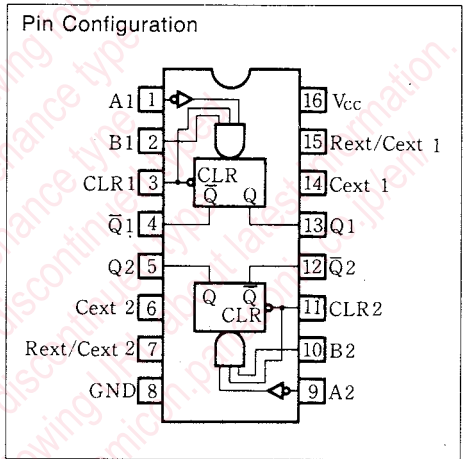
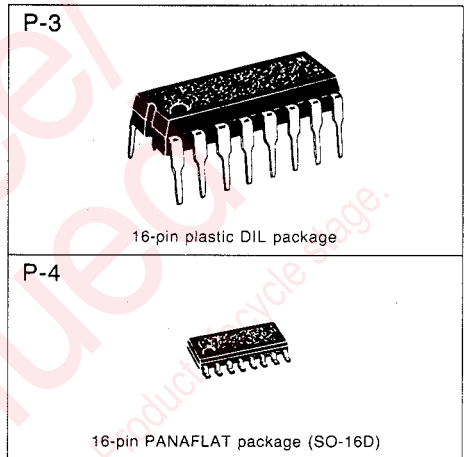
The trigger input triggers the respective multivibrator at the falling edge of the A input, rise of the B input, and rising edge of the CLR input, and once triggered, the output is kept in the monostable mode for a fixed period of time by the external resistor and condenser unless the level of the CLR input is set to "L".

Owing to the silicon gate CMOS process, these multivibrators have realized low power consumption and high noise immunity equivalent to those of a standard CMOS and the operation speed as high as an LS TTL. The MN74HC221/MN74HC221S can directly drive ten LS TTL inputs. To protect the input and output against electrostatic breakdown, a resistor and a diode are used for the  $V_{CC}$  and the GND. The pin configuration and the function are the same as those of the standard 54LS/74LS logic family.

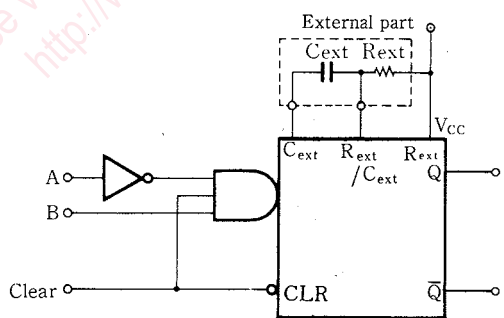
### Truth Table

Input			Output	
CLEAR	A	B	Q	$\bar{Q}$
L	X	X	L	H
X	H	X	L	H
X	X	L	L	H
H	L	$\nearrow$	$\square$	$\bar{\square}$
H	$\searrow$	H	$\square$	$\bar{\square}$
$\square$	L	H	$\square$	$\bar{\square}$

- Note) H : High level  
 : Low level  
 X : "H" or "L" either will do.  
 $\searrow$  : Trailing from "H" to "L"  
 $\nearrow$  : Leading from "L" to "H"  
 $\square$  : One piece of "H" level pulse  
 $\bar{\square}$  : One piece of "L" level pulse



### Logic Diagram



### ■ Absolute Maximum Ratings

Item		Symbol	Rating	Unit
Supply voltage		$V_{CC}$	-0.5~+7.0	V
Input output voltage		$V_I, V_O$	-0.5~ $V_{CC}+0.5$	V
Input protective diode current		$I_{IK}$	±20	mA
Output parasitic diode current		$I_{OK}$	±20	mA
Output current		$I_O$	±25	mA
Supply current		$I_{CC}, I_{GND}$	±50	mA
Storage temperature		$T_{stg}$	-65~+150	°C
Power dissipation	MN74HC221	$T_a = -40 \sim +60^\circ\text{C}$	400	mW
		$T_a = +60 \sim +85^\circ\text{C}$	Decrease to 200mW at the rate of 8mW/°C	
	MN74HC221S	$T_a = -40 \sim +60^\circ\text{C}$	275	mW
		$T_a = +60 \sim +85^\circ\text{C}$	Decrease to 200mW at the rate of 3.8mW/°C	

### ■ Recommended Operating Conditions

Item	Symbol	$V_{CC}(V)$	Rating	Unit
Operating power supply voltage	$V_{CC}$		2.0~6.0	V
Input output voltage	$V_I, V_D$		0~ $V_{CC}$	V
Operating temperature	$T_A$		-40~+85	°C
Input rise, fall time A, CLR	tr, tf	2.0	0~1000	ns
		4.5	0~5000	ns
		6.0	0~400	ns
Outer fitting timing resistance	$R_{ext}$		5~1000	kΩ
Outer fitting timing capacitance	$C_{ext}$		No limit	pF
Wiring capacitance	$R_{ext}/C_{ext}$		0~50	pF

### ■ DC Characteristics (GND=0V)

Item	Symbol	$V_{CC}$ (V)	Test Condition			Temperature					Unit
			$V_I$	$V_O$	Unit	$T_a = 25^\circ\text{C}$			$T_a = -40 \sim +85^\circ\text{C}$		
						min.	typ.	max.	min.	max.	
Input voltage high level	$V_{IH}$	2.0				1.5			1.5		V
		4.5				3.15			3.15		
		6.0				4.2			4.2		
Input voltage low level	$V_{IL}$	2.0						0.3		0.3	V
		4.5						0.9		0.9	
		6.0						1.2		1.2	
Output voltage high level	$V_{OH}$	2.0	$V_{IH}$	-20.0	μA	1.9	2.0		1.9		V
		4.5	or	-20.0	μA	4.4	4.5		4.4		
		6.0	or	-20.0	μA	5.9	6.0		5.9		
		4.5	$V_{IL}$	-4.0	mA	3.92			3.84		
		6.0		-5.2	mA	5.48			5.34		
Output voltage low level	$V_{OL}$	2.0	$V_{IH}$	20.0	μA		0.0	0.1		0.1	V
		4.5	or	20.0	μA		0.0	0.1		0.1	
		6.0	or	20.0	μA		0.0	0.1		0.1	
		4.5	$V_{IL}$	4.0	mA			0.26		0.33	
		6.0		5.2	mA			0.26		0.33	
Input leakage current	$I_I$	6.0	$V_I = V_{CC}$ or GND					±0.1		±1.0	μA
$R_{ext}/C_{ext}$ pin leakage current	$I_{OZ}$	6.0	$V_I = V_{IH}$ or $V_{IL}$ $V_O = V_{CC}$ or GND					±0.5		±5.0	μA
Static supply current	$I_{CC}$	6.0	$V_I = V_{CC}$ or GND, $I_O = 0$					8.0		80.0	μA

**■ AC Characteristics (GND=0V, Input transition time $\leq$ 6ns,  $C_L=50$ pF)**

Item	Symbol	$V_{CC}$ (V)	Test Condition	Temperature					Unit
				$T_a=25^\circ\text{C}$			$T_a=-40\sim+85^\circ\text{C}$		
				min.	typ.	max.	min.	max.	
Output rise time	$t_{TLH}$	2.0			27	75		95	ns
		4.5		10	15		19		
		6.0		8	13		16		
Output fall time	$t_{THL}$	2.0			20	75		95	ns
		4.5		8	15		19		
		6.0		6	13		16		
Propagation time A, B, CLR $\rightarrow$ Q, (L $\rightarrow$ H)	$t_{PLH}$	2.0			76	250		315	ns
		4.5		28	50		63		
		6.0		20	43		54		
Propagation time A, B, CLR $\rightarrow\bar{Q}$ , (H $\rightarrow$ L)	$t_{PHL}$	2.0			83	250		315	ns
		4.5		29	50		63		
		6.0		22	43		54		
Propagation time CLR $\rightarrow$ Q, $\bar{Q}$ (L $\rightarrow$ H)	$t_{PLH}$	2.0			47	150		190	ns
		4.5		16	30		38		
		6.0		15	26		33		
Propagation time CLR $\rightarrow\bar{Q}$ , $\bar{Q}$ (H $\rightarrow$ L)	$t_{PHL}$	2.0			44	150		190	ns
		4.5		15	30		38		
		6.0		15	26		33		
Minimum output pulse width	$t_{W(OUT)}$	2.0	C <sub>ext</sub> =0 R <sub>ext</sub> =5k $\Omega$		—				ns
		4.5		78					
		6.0		—					
Output pulse width*	$t_{W(OUT)}$	2.0	C <sub>ext</sub> =1000pF R <sub>ext</sub> =10k $\Omega$		—				$\mu\text{s}$
		4.5		4.8					
		6.0		—					
Input pulse width A, B	$t_{W(IN)}$	2.0				100		125	ns
		4.5		9	20		25		
		6.0			34		21		
Input pulse width CLR	$t_{W(IN)}$	2.0				200		250	ns
		4.5		21	40		50		
		6.0			34		43		

\* Output pulse width  $t_{W(OUT)}$  meets to the following formula when  $C_{ext}>1000$ pF

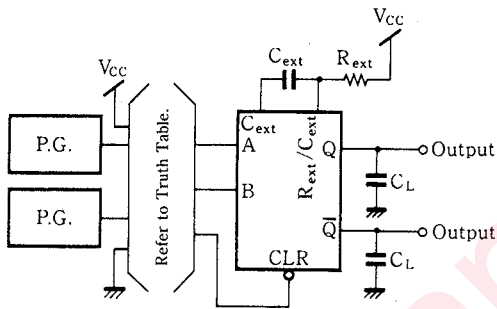
$$t_{W(OUT)} \approx 0.3 C_{ext} \cdot R_{ext}$$

**■ Caution in Use**

When using one circuit only, make CLR Low,  $R_{ext}/C_{ext}$ ,  $C_{ext}$ , Q,  $\bar{Q}$  open and keep other input pins High or Low.

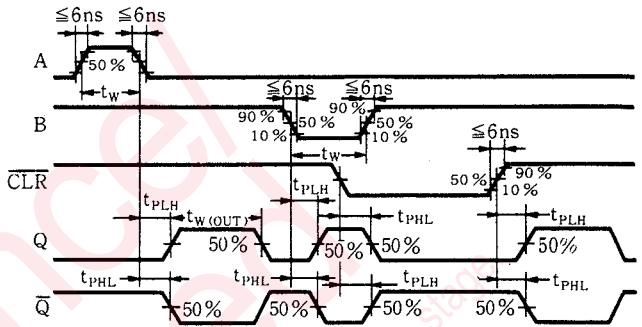
• Switching time measuring circuit and waveforms

1. Measuring circuit



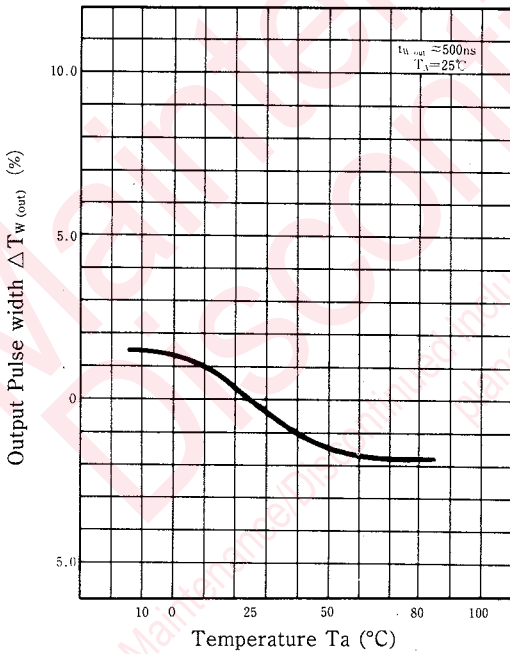
(Fig.1)

2. Switching waveforms

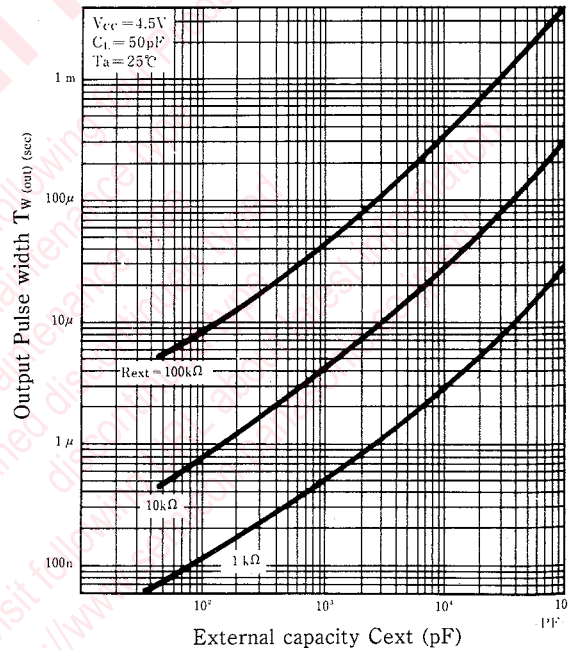


(Fig.2)

$\Delta T_{W(out)} \cdot T_a$  characteristics



$T_{W(out)} \cdot C_{ext}$  characteristics



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